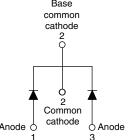




Vishay Semiconductors

Ultrafast Rectifier, 16 A FRED Pt®





Base common cathode 2							
Anode 0	Com) 2 imon iode	→ A 3	node			

PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 8 A					
V_{R}	400 V					
V _F at I _F	0.94 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





DESCRIPTION/APPLICATIONS

FRED Pt® series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V_{RRM}		400	V					
Average restified forward current			8						
Average rectified forward current total device	I _{F(AV)}	T _C = 155 °C, rated V _R	16	_					
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	100	А					
Peak repetitive forward current	I _{FRM}	T_C = 155 °C, rated V_R , square wave, 20 kHz	16						
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX.						
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	400	-	-			
Forward voltage	VF	I _F = 8 A	-	1.19	1.3	V		
	VF	I _F = 8 A, T _J = 150 °C	-	0.94	1.0			
Reverse leakage current I _R		$V_R = V_R$ rated	-	0.2	10			
		T _J = 150 °C, V _R = V _R rated	-	20	500	μΑ		
Junction capacitance	C _T	V _R = 400 V	-	14	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		



VS-16CTU04PbF, VS-16CTU04-N3

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DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 A, dI_F/dt =$	50 A/μA, V _R = 30 V	-	35	60		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	43	-	ns	
		T _J = 125 °C		-	67	-		
Peak recovery current		T _J = 25 °C	I _F = 8 A	-	2.8	-	^	
	IRRM	T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 200 \text{ V}$	-	6.3	-	- A	
Reverse recovery charge	0	T _J = 25 °C	11	=	60	-	nC	
	Q _{rr}	T _J = 125 °C		=	210	-	IIC	

THERMAL MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	S MIN. TYP.		MAX.	UNITS	
Maximum junction and temperature range	storage	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance,	per leg	В		-	3.6	4		
junction to case	per device	R_{thJC}		-	1.8	2		
Thermal resistance, junction to ambient		R _{thJA}	Typical socket mount	-	-	50	°C/W	
Thermal resistance, case to heatsink		R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	-	
Weight				-	2.0	-	g	
Weight				-	0.07	-	OZ.	
Mounting torque				6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device			Case style TO-220AB	16CTU04			•	



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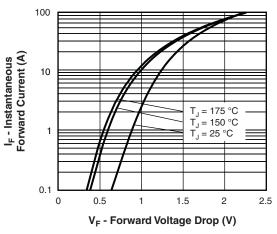


Fig. 1 - Typical Forward Voltage Drop Characteristics

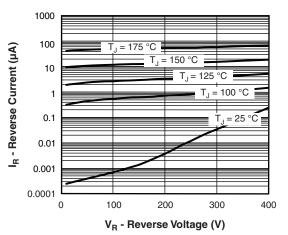


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

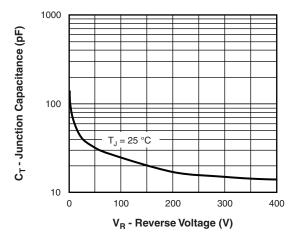


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

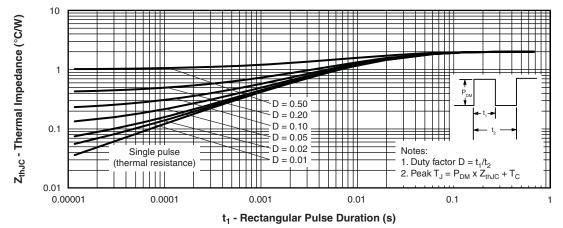


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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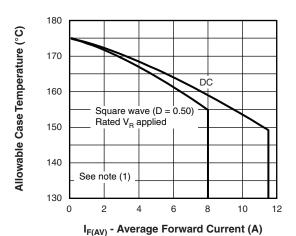


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

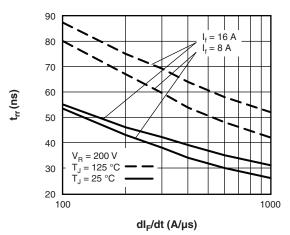


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

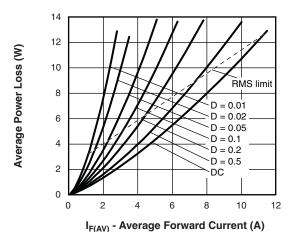


Fig. 6 - Forward Power Loss Characteristics

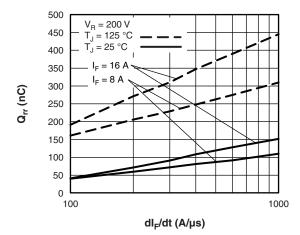


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (\text{see fig. 6}); \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ at \ V_{R1} = Rated \ V_R \\ \end{array}$

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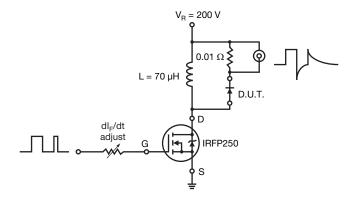
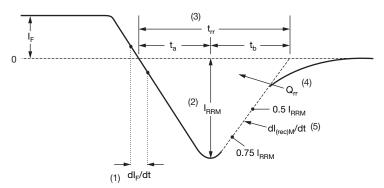


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

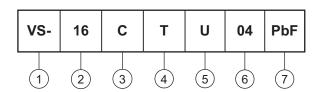
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-16CTU04PbF, VS-16CTU04-N3

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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Current rating (16 = 16 A)

3 - Circuit configuration:

C = common cathode

4 - Package:

T = TO-220

5 - Ultrafast recovery

6 - Voltage rating (04 = 400 V)

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-16CTU04PbF	50	1000	Antistatic plastic tube				
VS-16CTU04-N3	50	1000	Antistatic plastic tube				

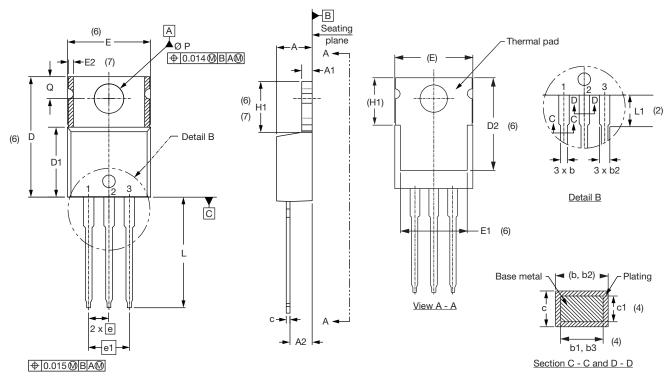
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95222</u>						
Part marking information	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				



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TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Lead assignments

<u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	
		•	•	•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Legal Disclaimer Notice



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